

MMDT2222A

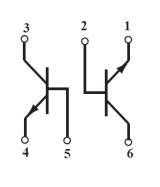
NPN/NPN Multi-Chip Transistor

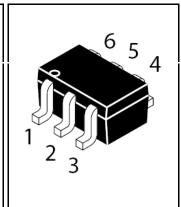
FEATURES

· Ideal for low power amplification and switching

MECHANICAL DATA

- Case: SOT-363 Plastic
- Case material: "Green" molding compound, UL flammability classification 94V-0, (No Br. Sb. Cl)
- Lead Free in RoHS 2002/95/EC Compliant





Maximum Ratings @ $T_A = 25^{\circ}C$

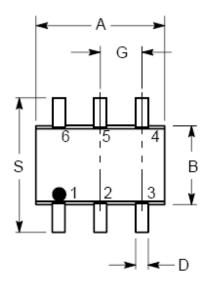
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I _C	600	mA
Total Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	$^{\circ}\!\mathbb{C}$
Storage Temperature Range	T _{STG}	-55~+150	$^{\circ}\!\mathbb{C}$

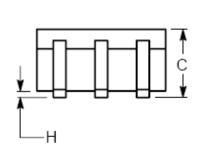
Electrical Characteristics @ T_A = 25 $^{\circ}$ C unless otherwise specified

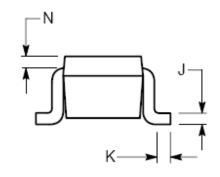
Characteristic	Test Condition	Symbol	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	$I_{C}=10\mu A, I_{E}=0$	V_{CBO}	75			V
Collector-emitter breakdown voltage	I _C =10mA,I _B =0	V_{CEO}	40			V
Emitter-base breakdown voltage	I _E =10μA,I _C =0	V_{EBO}	6			V
Collector-base cut-off current	$V_{CB} = 60V, I_{E} = 0$	I _{CBO}			0.01	uA
Emitter-base cut-off current	V_{EB} =3 V , I_{C} =0	I _{EBO}			0.1	uA
	V _{CE} =10V,I _C =0.1mA	h _{FE1}	35			
DC current gain	V _{CE} =10V,I _C =1mA	h _{FE2}	50			
	V _{CE} =10V,I _C =10mA	h _{FE3}	75			
	V _{CE} =10V,I _C =150mA	h _{FE4}	100		300	
	V _{CE} =1V,I _C =150mA	h _{FE5}	50			
	V _{CE} =10V,I _C =500mA	h _{FE5}	40			
Collector-emitter saturation voltage	I _C =150mA,I _B =15mA	V _{CE} (sat)1			0.3	V
	I _C =500mA,I _B =50mA	V _{CE} (sat)2			1.0	V
Base-emitter saturation voltage	I _C =150mA,I _B =15mA	V _{BE} (sat)1	0.60		1.2	V
	I _C =500mA,I _B =50mA	V _{BE} (sat)2			1.0	V
Transition frequency	V _{CE} =20V,I _C =20mA, f=100MHz	f⊤	300			MHz
Collector output capacitance	V _{CB} =10V,I _E =0,f=1MHz	Cob			8	pF
Noise figure	V_{CE} =10V, I_{C} =0.1mA, f =1kHz, R_{S} =1K Ω	NF			4	dB
Delay time	V _{CC} =30V, V _{BE} =-0.5V	T_d			10	nS
Rise time	I _C =150mA , I _{B1} =-I _{B2} =15mA	T _r			25	nS
Storage time	V _{CC} =30V, I _C =150mA	Ts			225	nS
Fall time	I _{B1} =-I _{B2} =15mA	T _f			60	nS

REV. 0, Jan-2013, KSTR11

SOT-363 Outline Dimension







Symbol	Dimension In Millimeters			
Syllibol	Min	Max.		
Α	1.89	2.20		
В	1.15	1.35		
С	0.80	1.10		
D	0.10	0.30		
G	0.65 BSC			
Н		0.10		
J	0.10	0.25		
K	0.10	0.30		
N	0.20 REF			
S	2.00	2.20		

Device Marking:

Device P/N	Marking code
MMDT2222A	XX

RATING AND CHARACTERISTIC CURVES MMDT2222A



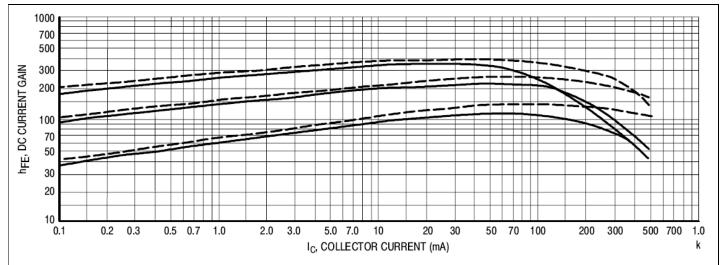


Figure 1. DC Current Gain

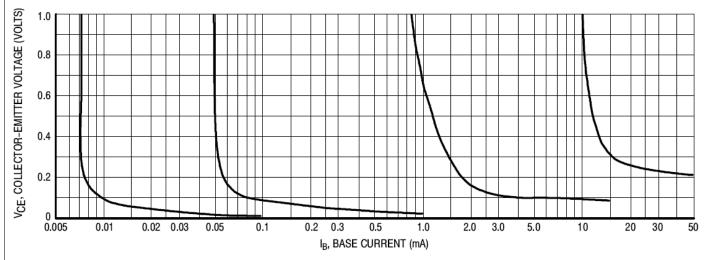


Figure 2. Collector Saturation Region

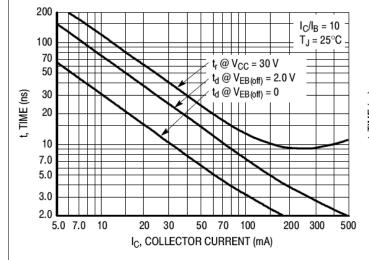


Figure 3. Turn-On Time

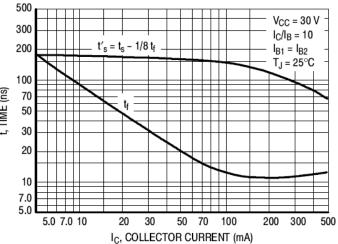
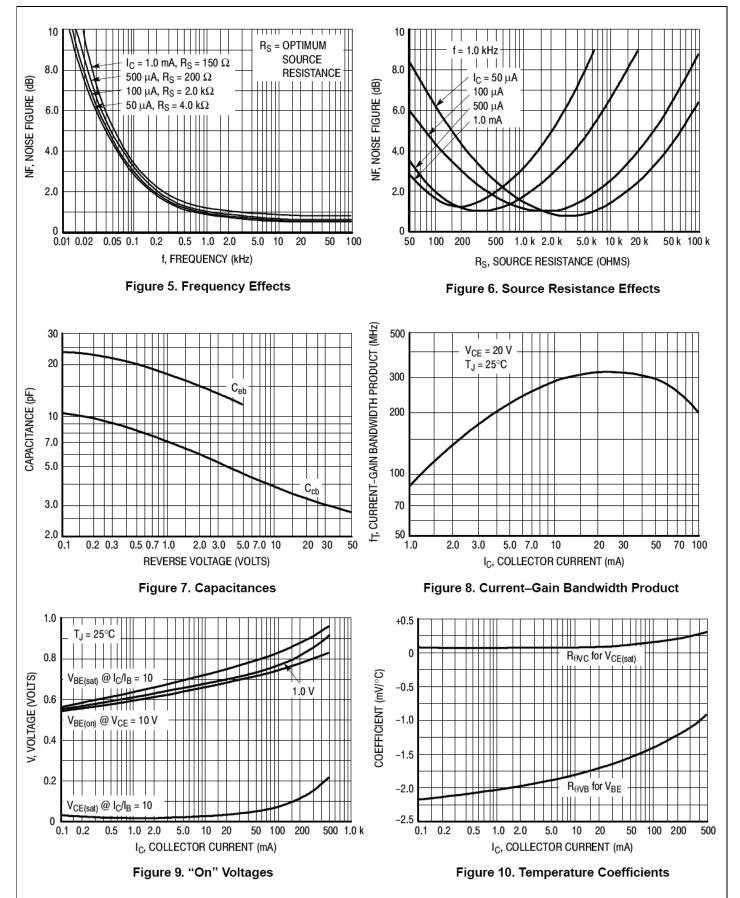


Figure 4. Turn-Off Time

RATING AND CHARACTERISTIC CURVES MMDT2222A







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New Marking Rule Notification

Range: In order to have well management in process control, the new marking rule is applied to small signal device including Switching Diode, Transistor and Schottky Diode.

Package: SOT-363

